PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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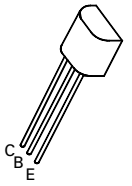
ZTX537C



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-800	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	750	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +175	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	I_C=-100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-45			V	I_C=-100μA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_E=0
Collector Cut-Off Current	I_{CBO}			-100	nA	V_{CB}=-45V
Emitter Cut-Off Current	I_{EBO}			-0.2	μA	V_{EB}=-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.7	V	I_C=-500mA, I_B=-50mA*
Base-Emitter Saturation Voltage	$V_{BE(on)}$			-1.2	V	I_C=-300mA, V_{CE}=-1V*
Static Forward Current Transfer Ratio	h_{FE}	250 170		630		I_C=-100mA, V_{CE}=-1V* I_C=-300mA, V_{CE}=-1V*
Transition Frequency	f_T		200		MHz	I_C=-10mA, V_{CE}=-5V f=50MHz
Output Capacitance	Cobo		12		pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%